

Product data sheet

1. General description

Planar passivated high commutation triac in a SOT223 surface mounted plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

2. Features and benefits

- · 3Q technology for improved noise immunity
- Direct triggering from low power drivers and logic ICs
- High commutation capability with sensitive gate
- High immunity to false turn-on by dV/dt
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Surface mountable package
- Triggering in three quadrants only

3. Applications

- General purpose motor control
- Small loads in washing machines
- Solenoid drivers

4. Quick reference data

.

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 106 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	1	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms	-	-	13.7	A
		full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	-	12.5	A
Tj	junction temperature		-	-	125	°C
Static chara	acteristics	·				
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 9</u>	1	-	10	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 9</u>	1	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 9</u>	1	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	-	12	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.2	1.5	V
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit; Fig. 14	600	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	V_D = 400 V; T _j = 125 °C; I _{T(RMS)} = 1 A; dV _{com} /dt = 20 V/µs; (snubberless condition); gate open circuit	2.5	-	-	A/ms
		V_D = 400 V; T _j = 125 °C; I _{T(RMS)} = 1 A; dV _{com} /dt = 10 V/µs; gate open circuit	3.5	-	-	A/ms

5. Pinning information

Table 2.	Pinning in	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2-T1
2	T2	main terminal 2		sym051
3	G	gate		Symoor
4	T2	main terminal 2	☐1 ☐2 ☐3 SC-73 (SOT223)	

6. Ordering information

Table 3. Ordering infor	mation		
Type number	Package		
	Name	Description	Version
BTA201W-600E	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 106 \text{ °C}$; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	1	A
I _{TSM}	non-repetitive peak on-	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	13.7	А
	state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	12.5	A
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.78	A²s
dl _T /dt	rate of rise of on-state current	I _G = 0.2 A	-	100	A/µs
I _{GM}	peak gate current		-	1	А
P _{GM}	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
T _i	junction temperature		-	125	°C

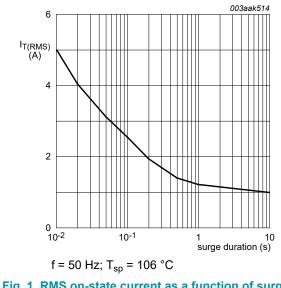


Fig. 1. RMS on-state current as a function of surge duration; maximum values

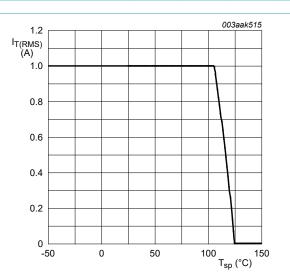
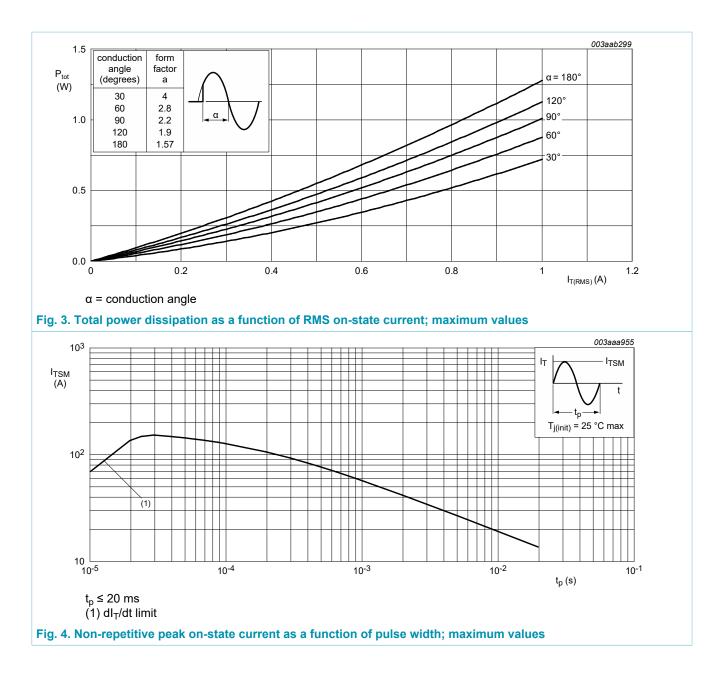


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

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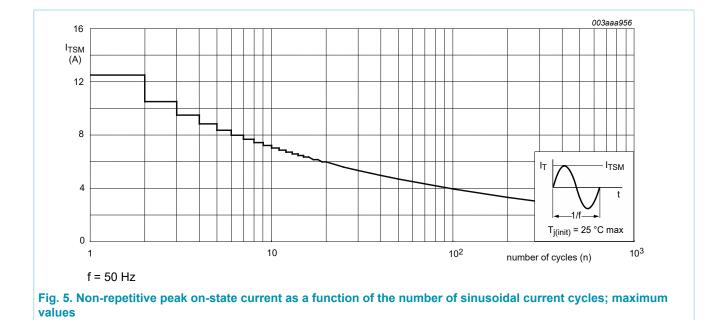
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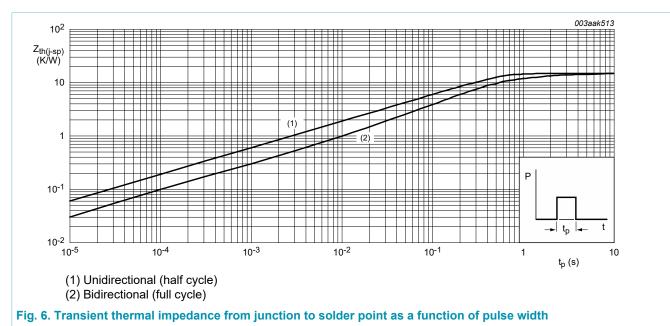
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8. Thermal characteristics

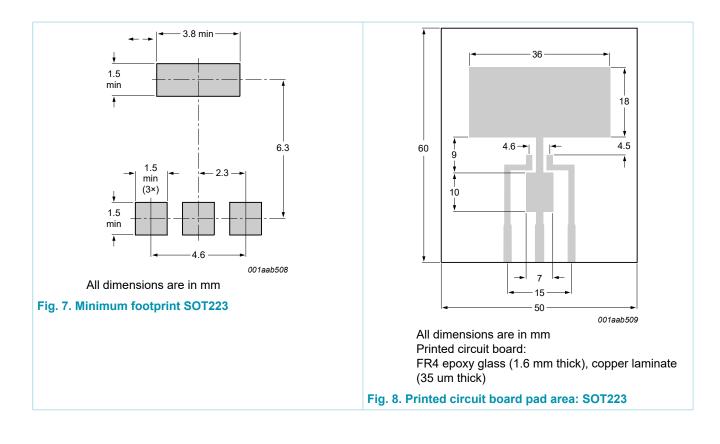
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	full and half cycle; <u>Fig. 6</u>	-	-	15	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air; printed circuit board mounted; minimum footprint; Fig. 7	-	156	-	K/W
		in free air; printed circuit board mounted; pad area; Fig. 8	-	70	-	K/W



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9. Characteristics

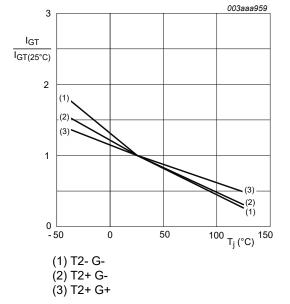
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		· · · ·			
I _{GT}	gate trigger current	V_D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 9</u>	1	-	10	mA
		V_D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 9</u>	1	-	10	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2- G-};$ T _j = 25 °C; Fig. 9	1	-	10	mA
ΙL	latching current	$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-};$ T _j = 25 °C; <u>Fig. 10</u>	-	-	12	mA
		V_D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 10</u>	-	-	12	mA
		V_D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 10</u>	-	-	12	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	-	12	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.2	1.5	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 13	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 13	0.2	0.3	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics	· · · · ·				
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit; Fig. 14	600	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T _j = 125 °C; I _{T(RMS)} = 1 A; dV _{com} /dt = 20 V/µs; (snubberless condition); gate open circuit	2.5	-	-	A/m
		V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 1 A; dV _{com} /dt = 10 V/µs; gate open circuit	3.5	-	-	A/ms

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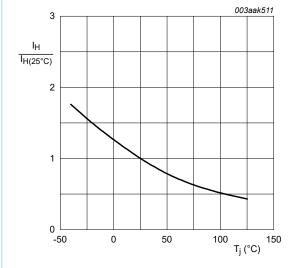
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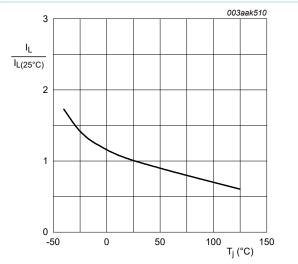
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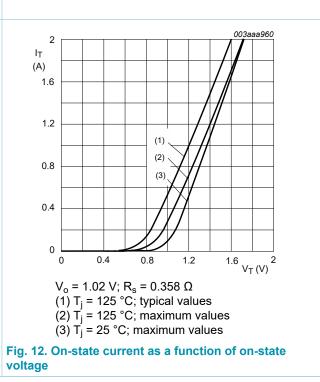








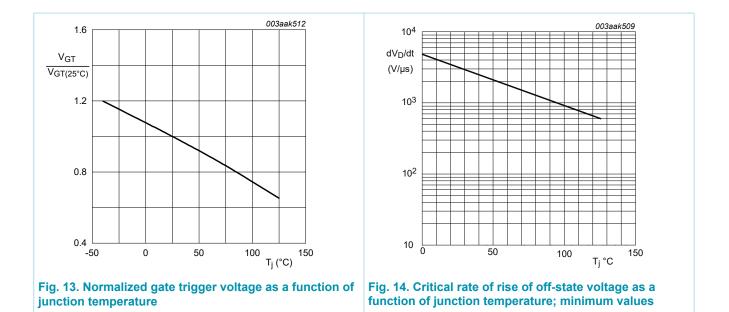




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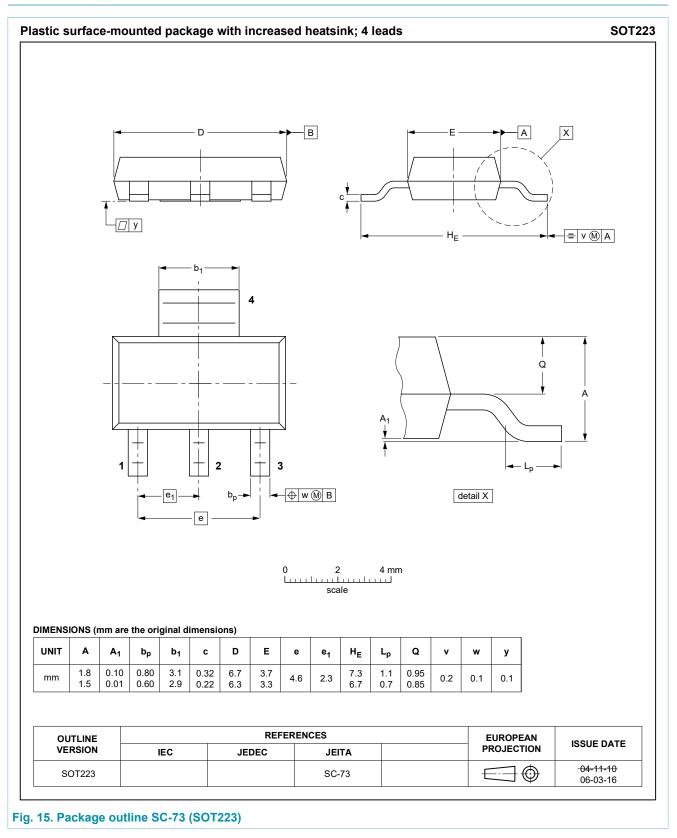


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10. Package outline



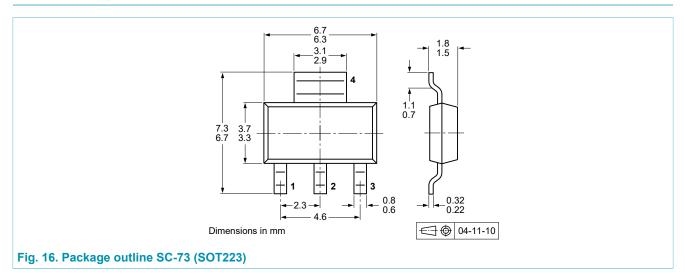
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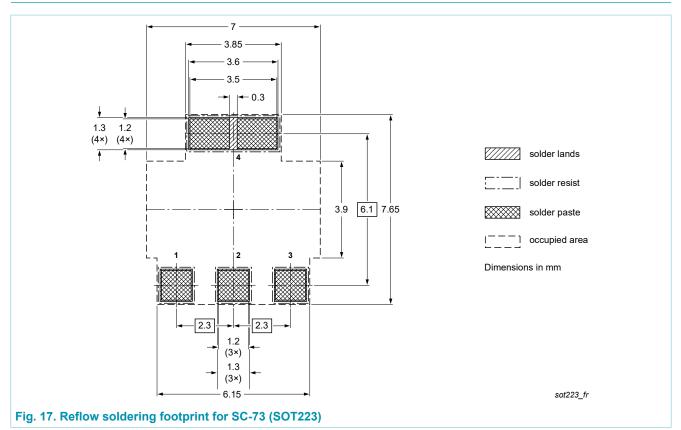
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11. Package outline (minimized)



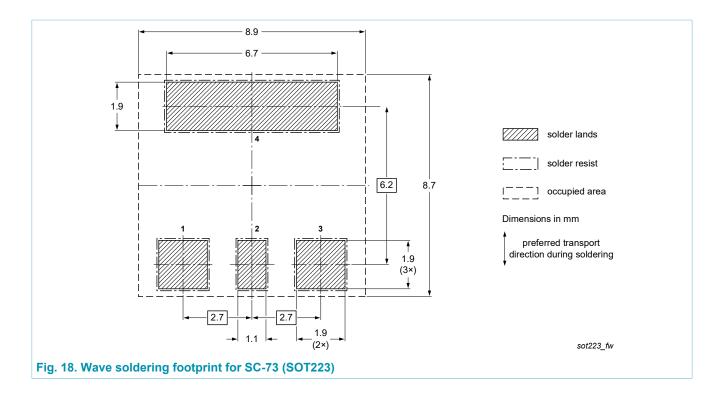
12. Soldering



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13. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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